

FEATURES

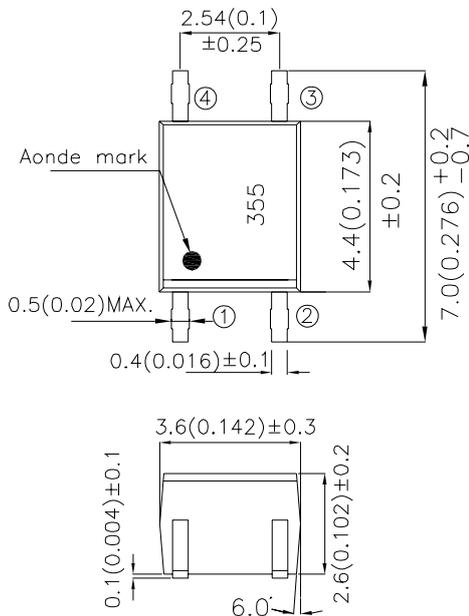
- 1.High current transfer ratio.
- 2.Opaque type, mini-flat package.
- 3.Subminiature type (The volume is smaller than that of our conventional DIP type by as far as 30%).
- 4.Isolation voltage between input and output Viso:3750Vrms.
- 5.Employs double transfer mold technology.
- 6.Recognized by UL and CUL, file NO.E225308.
- 7.Approved by VDE 0884 Teil2(NO:40017614).
- 8.Package : 1000Pcs / Reel.
- 9.Rohs compliant.

APPLICATIONS

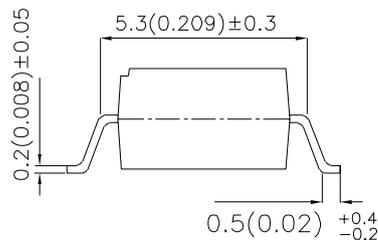
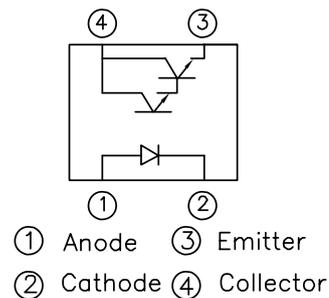
- 1.Hybrid substrates that require high density mounting.
- 2.Programmable controllers.

*PACKAGE DIMENSIONS (UNIT:mm)

SMD Type



Internal connection diagram



UNIT : MM[INCH]
 TOLERANCE : ±0.5[±0.02] UNLESS OTHERWISE NOTED.



*Absolute Maximum Ratings (TA=25°C)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I _F	50	mA
	Reverse voltage	V _R	6	V
	Power dissipation	P	70	mW
Output	Collector-emitter voltage	V _{CEO}	35	V
	Emitter-collector voltage	V _{ECO}	6	V
	Collector current	I _C	80	mA
	Collector power dissipation	P _C	150	mW
Total power dissipation		P _{tot}	170	mW
* ¹ Isolation voltage		V _{iso}	3750	V _{rms}
Operating temperature		T _{opr}	-30 to +100	°C
Storage temperature		T _{stg}	-40 to +125	°C
* ² Soldering temperature		T _{sol}	260	°C

*¹ 40 to 60% RH, AC for 1 minute.

*² For 10 seconds.

*Electro-optical Characteristics

	Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Input	Forward voltage	V _F	I _F =20mA	-	1.2	1.4	V	
	Peak forward voltage	V _{FM}	I _{FM} =0.5A	-	-	3.0	V	
	Reverse current	I _R	V _R =4V	-	-	10	uA	
Output	Collector dark current	I _{CEO}	V _{CE} =10V, I _F =0	-	-	10 ⁻⁶	A	
	Collector-emitter breakdown voltage	BV _{CEO}	I _C =0.1mA, I _F =0	35	-	-	V	
	Emitter-collector breakdown voltage	BV _{ECO}	I _E =10uA, I _F =0	6	-	-	V	
Transfer Characteristics	Current transfer ratio	CTR	I _F =1mA, V _{CE} =2V	600	1600	7500	%	
	Collector-emitter saturation voltage	V _{CE(sat)}	I _F =20mA, I _C =1mA	-	0.8	1.0	V	
	Response time	Rise time	T _r	V _{CE} =2V, I _C =2mA R _L =100Ω	-	60	300	uS
		Fall time	T _f		-	53	250	uS

Fig. 1 Current Transfer vs. Forward Current

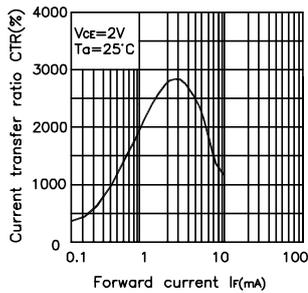


Fig. 2 Forward Current vs. Forward Voltage

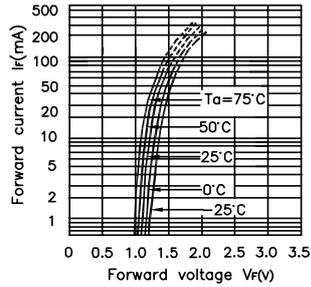


Fig. 3 Collector Current vs. Collector-emitter Voltage

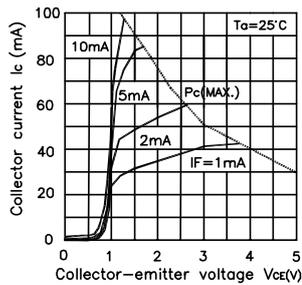


Fig. 4 Forward Current vs. Ambient Temperature

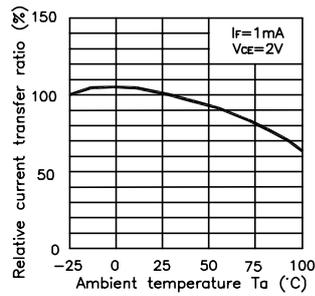


Fig. 5 Collector-emitter Saturation Voltage vs. Ambient Temperature

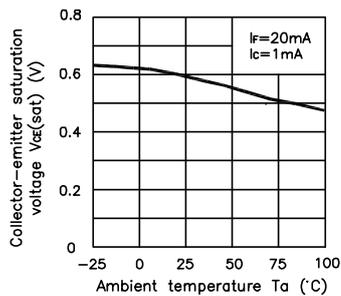


Fig. 6 Response Time vs. Load Resistance

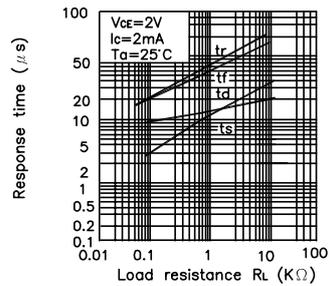


Fig. 7 Collector-emitter Saturation Voltage vs. Forward Current

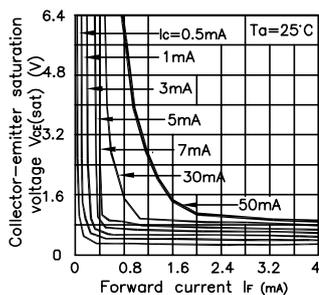
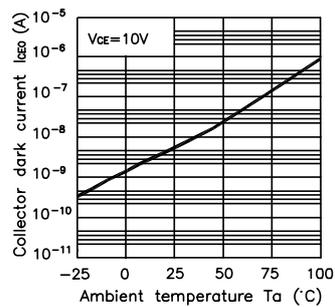
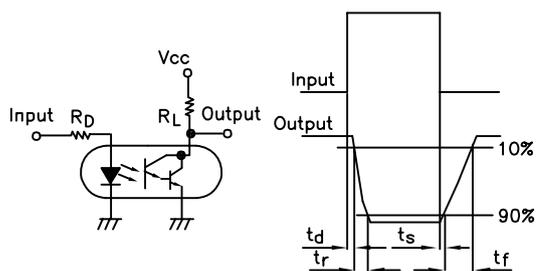


Fig. 8 Collector Dark Current vs. Ambient Temperature



Test Circuit for Response Time



* NOTES ON HANDLING

1.Recommended soldering conditions (Dip soldering)

(1) Dip soldering

Temperature	260 or below (molten solder temperature)
Time	Less than 10 seconds.
Cycle	One cycle allowed to be dipped in solder including plastic mold portion.
Flux	Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

(2) Cautions

Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2.Cautions regarding noise

Be aware that power is suddenly into the component any surge current may cause damage happen, even if the voltage is within the absolute maximum ratings.

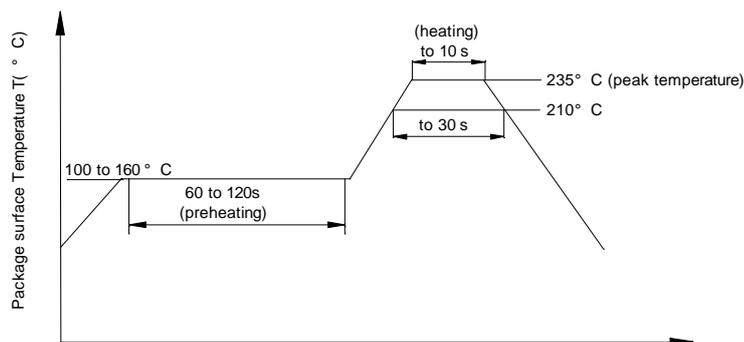
NOTES ON HANDLING

1.Recommended soldering conditions

(1).Infrared reflow soldering

- Peak reflow temperature 235 ° C or below(package surface temperature)
- Time of temperature higher than 210 ° C 30 seconds or less
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine(The flux with a maximum chlorine content of 0.2Wt % is recommended.)

Recommended Temperature Profile of infrared Reflow



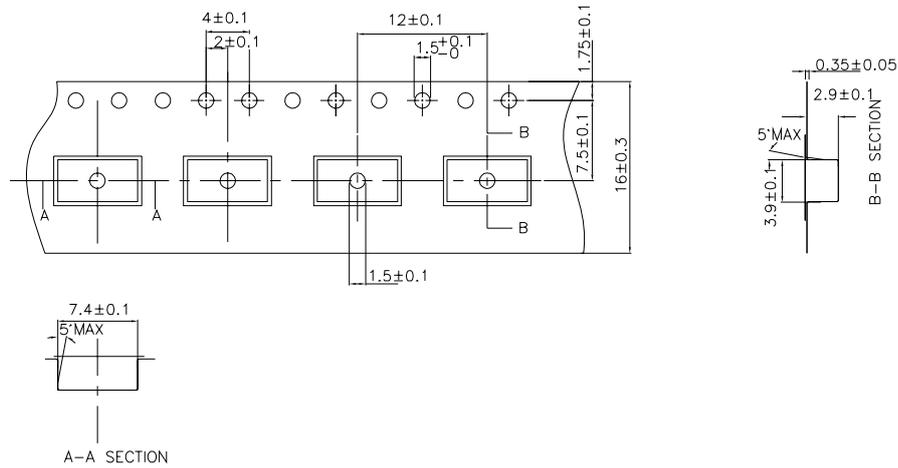
CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them.

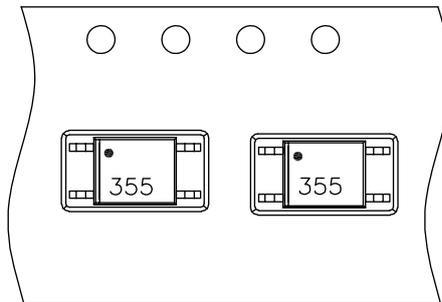
RESTRICTIONS ON PRODUCT USE

- The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices / types available in every country.
- We mention about our product quality stability, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing KINGBRIGHT products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a KINGBRIGHT product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that KINGBRIGHT products are used within specified operating ranges as set forth in the most recent products specifications.

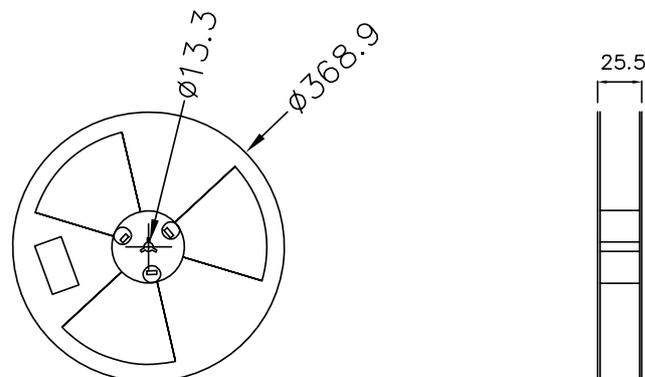
Outline and Dimension(Tape) (Units : mm)



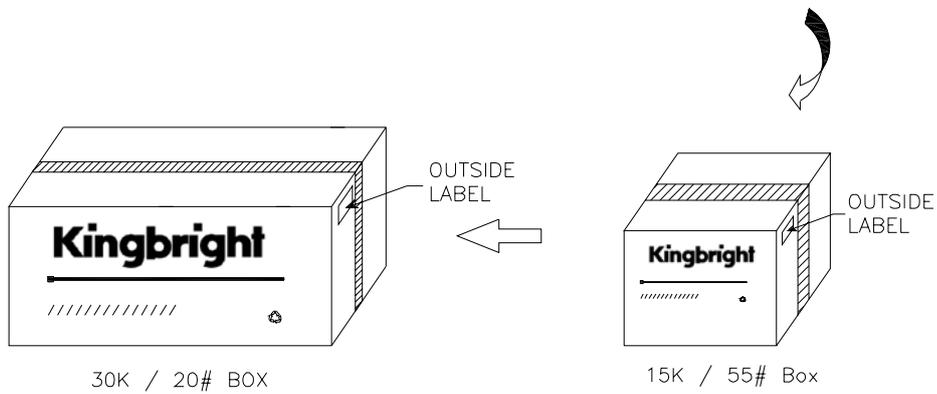
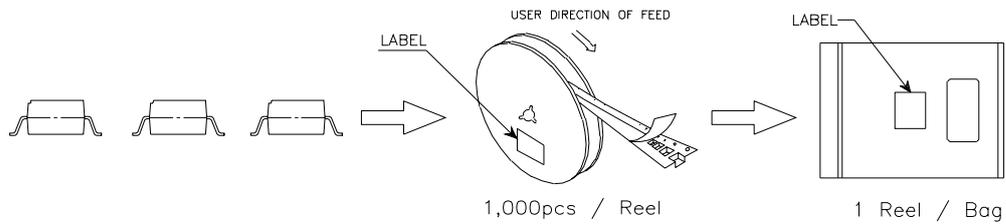
Tape Direction



Outline and Dimension(Reel)



Packing: 1000pcs/reel



Kingbright	
P/N : KB355NT	
QTY: 1,000 pcs	Q.C. Q C xx xx. xxxx PASSED
S/N: XXXX	
CODE: XXX	
LOT NO:	
	
MADE IN CHINA	RoHS Compliant